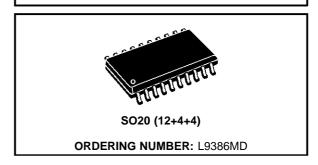


DUAL INTELLIGENT POWER LOW SIDE SWITCH

- DUAL POWER LOW SIDE DRIVER WITH 2 x 5A
- LOW R_{DSON} TYPICALLY $200m\Omega$ @ T_J = 25° C
- INTERNAL OUTPUT CLAMPING DIODES V_{FB}=50V FOR INDUCTIVE RECIRCULATION
- LIMITED OUTPUT VOLTAGE SLEW RATE FOR LOW EMI
- µP COMPATIBLE ENABLE AND INPUT
- WIDE OPERATING SUPPLY VOLTAGE RANGE 4.5V TO 45V
- REAL TIME DIAGNOSTIC FUNCTIONS
 - OUTPUT SHORTED TO GND
 - OUTPUT SHORTED TO VSS
 - OPEN LOAD
 - LOAD BYPASS
 - OVERTEMPERATURE
- DEVICE PROTECTION FUNCTIONS
 - OVERLOAD DISABLE
 - REVERSE BATTERY UP TO -16V @ Vs
 - THERMAL SHUTDOWN

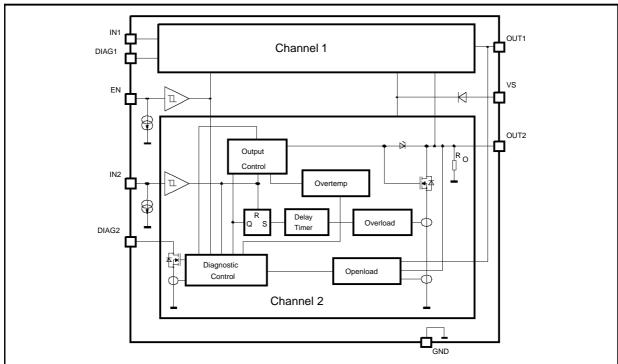
MULTIPOWER BCD TECHNOLOGY



DESCRIPTION

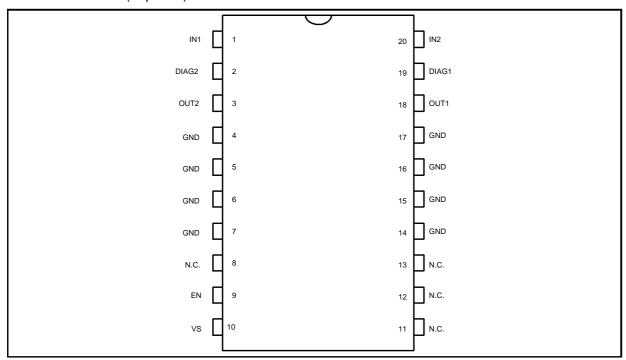
The L9386MD is a monolithic integrated dual low side driver realized in an advanced Multipower-BCD mixed technology. It is especially intended to drive valves in automotive environment. Its inputs are μP compatible for easy driving. Particular care has been taken to protect the device against failures, to avoid electro-magnetic interferences and to offer extensive real time diagnostic.

BLOCK DIAGRAM



January 1995 1/10

PIN CONNECTION (Top view)



ABSOLUTE MAXIMUM RATINGS (no damage or latch)

Symbol	Parameter	Value	Unit
VS _{DC}	DC supply voltage	-16 to 45	V
VS _{TR}	Transient supply voltage (t ≤ 500ms)	60	V
$V_{IN,EN}$	Input voltage (≤ 10mA)	-1.5 to 6	V
VD_{DC}	Diagnostic DC output voltage (≤ 50mA)	-0.3 to 16	V
VO_{DC}	DC output voltage	45	V
VO_{TR}	Transient output voltage ($R_L \ge 4\Omega$)	60	V
lo	Output load current	internal limited	
I _{OR}	Reverse output current limited by load	-4	Α
EO	Switch-off energy for inductive loads ($t_{EO} = 250\mu s$, T = 5ms)	50	mJ
T _{iEO}	Junction temperature during switch-off $\sum t = 30$ min	175	°C
Tj	Junction temperature	-40 to +150	°C
Ta	Storage temperature	-55 to +150	°C

THERMAL DATA

Symbol	Parameter	Value	Unit
T _{jDIS}	Thermal disable junction temperature threshold	160 to 190	°C
R _{th j-pins}	Thermal resistance junction to pins	14	°C/W

ELECTRICAL CHARACTERISTICS (Operating Range) - The electrical characteristics are valid within the below defined operative range, unless otherwise specified.

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Unit
V_S	Board supply voltage		4.5	12	32	V
V_D	Stabilized diagnostic output voltage		-0.3	5	16	V
Tj	Junction Temperature		-40		150	°C

ELECTRICAL CHARACTERISTICS (continued)

Symbol	Parameter	Test Condition	Value T _{i1}			Unit	
1			Min.	Тур.	Max.	1	
IS _{SB}	Static standby supply current	b) c) V _{EN} = L, VO ≤ VO _{uv}		0.73	1.5 15	mA mA	
IS	DC supply current	b) c) V _{EN} = V _{IN} = H		1.3	5 15	mA mA	
VDL	Diagnostic ouput low voltage	b) I _D = 2mA c) I _D = 1mA		0.35	0.5	V	
ID _{LE}	Diagnostic output leakage current	VS = 0V or $VS = open$; $VD = 5.5V$ $T_j \le 125^{\circ}C$		0.1	2	μΑ	
ID	Diagnostic output current capability	VD ≤ 16V DIAG = L	2	6	30	mA	
VOuv	Open load voltage threshold	V _{EN} = X, V _{IN} = L	0.51 x VS	0.55 x VS	0.59 x VS	V	
threshold		b) VEN = X, $V_{IN1,2}$ = L VS \geq VO _C \geq VO _{UV} VO _C = output voltage of other channel c)	VO _C - 0.9V VO _C -	VO _C - 1.25V VO _C -	VO _C - 1.6V	V ¹⁾	
IOuc	Open load current threshold	a) V _{FN} = V _{IN} = H	0.7V 100	1.25V 320	1.8V 480	mA	
1000	open load current uneshold	c)	20	320	400	mA	
IO _{OC}	Over load current threshold	b)	5	7		Α	
VO _{CL}	Output voltage during clamping	IO _{CL} ≥ 100mA	45	52	60	V	
S _{ON,OFF}	Output (fall, rise) slew rate	a) Fig. 2	200	1500	3200	V/ms	
R _{IO}	Internal output pull down resistor	V _{EN} = L	10	20	40	ΚΩ	
R _{DSON}	Output on resistance	VS > 9.5V IO = 2A $T_j = 25^{\circ}C$ $T_j = 150^{\circ}C$		200	300 500	$m\Omega$	
V _{(EN,IN)L} Logic input low voltage		I _{EN, IN} ≤ 10mA b) c)	-1.5 -1.5		1 0.5	V V	
$V_{(EN,IN)H}$	Logic input high voltage		2.2		5.5	V	
$V_{(EN,IN)hys}$	Logic input hysteresis		0.2	0.4	1	V	
I _{EN}	Enable input sink current	$1V \le V_{EN} \le 5.5V$	10	30	60	μΑ	
I _{IN} Logic input sink current		$1V \leq V_{IN} \leq 5.5V$	40	95	180	μΑ	
t _{D ON}	Output delay ON time	a) Fig. 2		4	25	μS	
t _{D OFF}	Output delay OFF time	a) Fig. 2	5	15	30	μs	
t _{D H-L, Diag.}	Diag. delay output OFF time	a) Fig. 2	5	30	65	μs	
t _{D IOu}	Diagnostic open load delay time	a) Fig. 4		8	50	μs	
t _{DOL}	Diagnostic overload delay switch-off time	a) Fig. 1	50	160	300	μs	

a) $9V \le Vs \le 16V$ (Nominal operating range)

 $R_L \le 6\Omega$,

 $I_0 \le IO_{OC}$



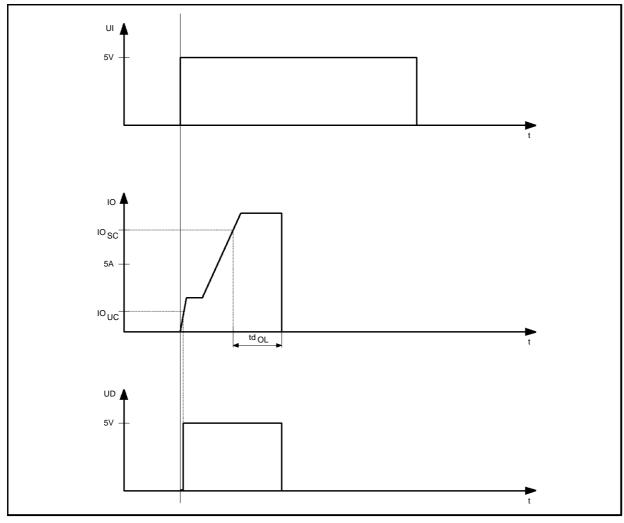
b) $6.5V \le V_S \le 16V$ (Diagnostic operation range) c) $4.5V \le V_S \le 6.5V$ and $16V < V_S \le 32V$ (Extended operation range) 1) Limit under evaluation.

DIAGNOSTIC TABLE (Operating range: $4.5V \le V_S \le 32V$)

Cond	litions	EN	IN	Out	Diag.
Normal function		L H H	X L H	off off on (*)	ILL
GND short	$VO_{typ} < 0.55V$	L	Х	off	Н
Load bypass	Δ VO _{1,2} ≥ 1.25V	Н	L	off	Н
Open load	IO _{typ} < 320mA	Н	Н	on (*)	L
T _{j typ} ≥ 175°C Oertemperature (**)		X X	L H	off off	ΗL
Latched Over load IO _{min} > 5A		Х	Н	off	L
Reset over load latch		Х	/	D.C.	D.C.

^(*) for $4.5V \le VS < 6.5V$, $IO \le 2A$ diag. table is valid.

Figure 1: Diagnostic overload delay time



^(**) If one diag. status shows the overtemp. recognition, in parallel this output will be switched OFF internally. The corresponding channel should be switched OFF additional by its Input or ENABLE signal, otherwise the overload latch will be set after tool is passed. This behaviour will be related to the overdrop sensing which will be used as over load recognition.

Figure 2: Output slope.

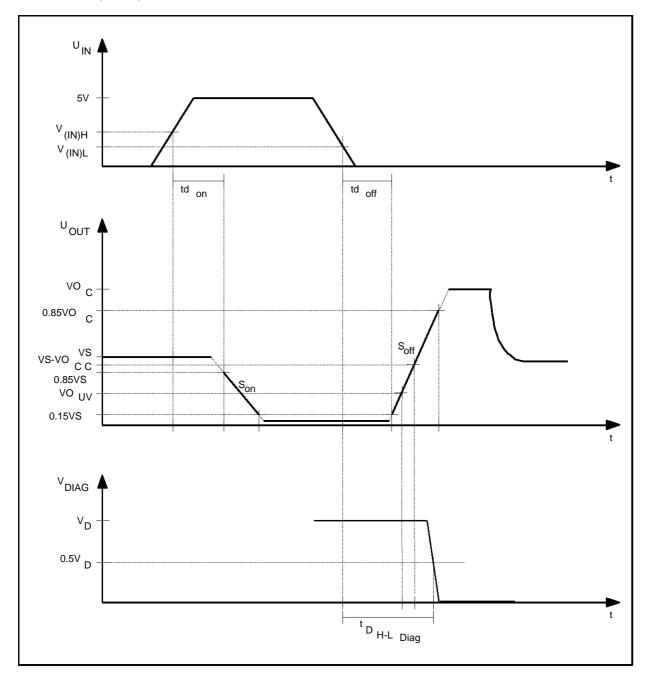


Figure 3: Block diagram - Open load voltage detection.

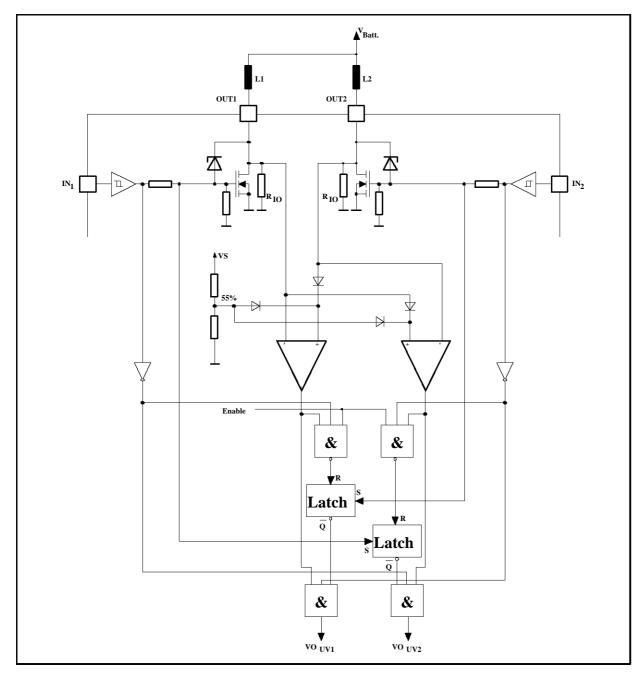
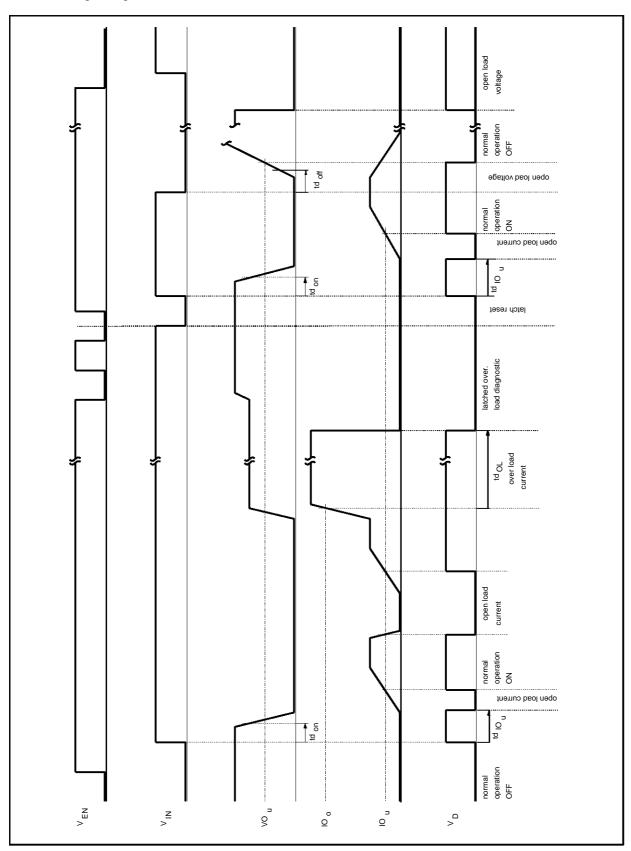


Figure 4: Logic diagram.



CIRCUIT DESCRIPTION

The L9386MD is a dual low side driver for inductive loads like valves in automotive environment. The device is enabled by a common CMOS compatible ENABLE high signal. The internal pull down current sources at the ENABLE and INPUT pins protect the device in open input conditions against malfunctions. An output slope limitation for du/dt is implemented to reduce the EMI. An integrated active flyback voltage limitation clamps the output voltage during the flyback phase to 50V.

Each driver is protected against short circuit and thermal overload. In short circuit condition the output will be disabled after a short delay time t_{DOL} to suppress spikes. This disable is latched until a negative slope occure at the correspondent input pin. The thermal disable for $T_J > 175\,^{\circ}\text{C}$ of the output will be reseted if the junction temperature decreases about 20 $\,^{\circ}\text{C}$ below the disable threshold temperature.

For the real time error diagnosis the voltage and the current of the outputs are compared with internal fixed values VOUV for OFF and IOUC for ON conditions to recognize open load ($R_L \ge 20 K\Omega$, $R_L > 38\Omega$) in ON and OFF conditions. The diagnostic

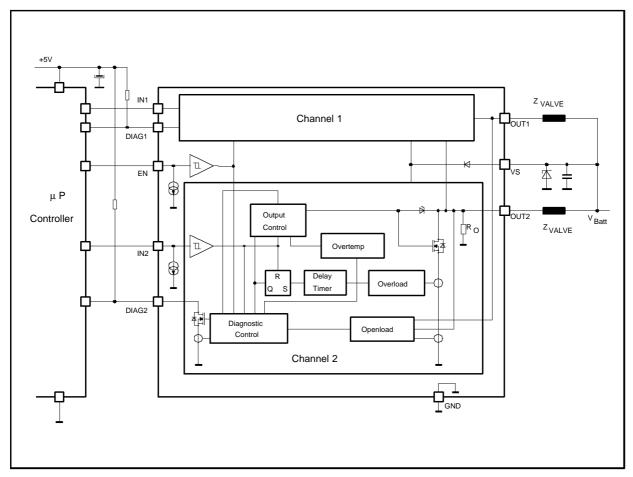
Figure 5: Application circuit diagram.

operates also in the extended supply voltage rang of $4.5V \le VS \le 32V$.

Also the output voltages VO_{1,2} are compared against each other in OFF condition with a fixed offset of ΔVO_{UV} 1,2 to recognize GND bypasses. To suppress mail ΔVO diagnoses during the flyback phases of the compared output, the ΔVO diagnostic includes a latch function. Reaching the flyback clamping voltage VOc the diagnostic signal is reseted by a latch. To activate again this kind of diagnostic a low signal at the correspondent INPUT or the ENABLE pin must occur (see also Fig.3).

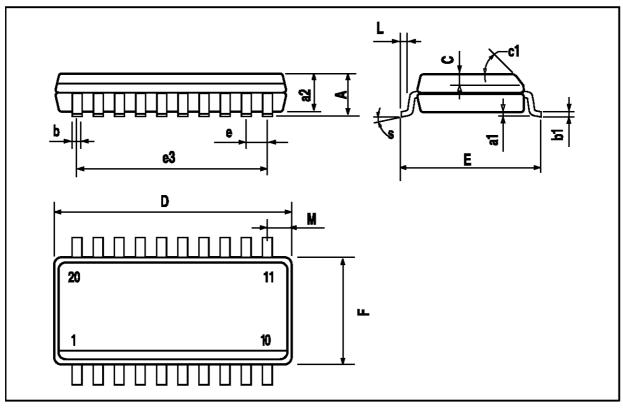
The diagnostic output level in connection with different ENABLE and INPUT conditions allows to recognize different fail states, like overtemp, short to VSS, short to GND, bypass to GND and disconnected load (see also page 7 diagnostic table).

The diagnostic output is also protected against short to UD_{max} . Oversteping the over load current threshold IO_0 , the output current will be limited internally during the diagnostic overload delay switch-off time t_{DOL} .



SO20 PACKAGE MECHANICAL DATA

DIM.	mm			inch			
Diwi.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А			2.65			0.104	
a1	0.1		0.3	0.004		0.012	
a2			2.45			0.096	
b	0.35		0.49	0.014		0.019	
b1	0.23		0.32	0.009		0.013	
С		0.5			0.020		
c1			45 ((typ.)			
D	12.6		13.0	0.496		0.512	
Е	10		10.65	0.394		0.419	
е		1.27			0.050		
e3		11.43			0.450		
F	7.4		7.6	0.291		0.299	
L	0.5		1.27	0.020		0.050	
М			0.75			0.030	
S	8 (max.)						



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